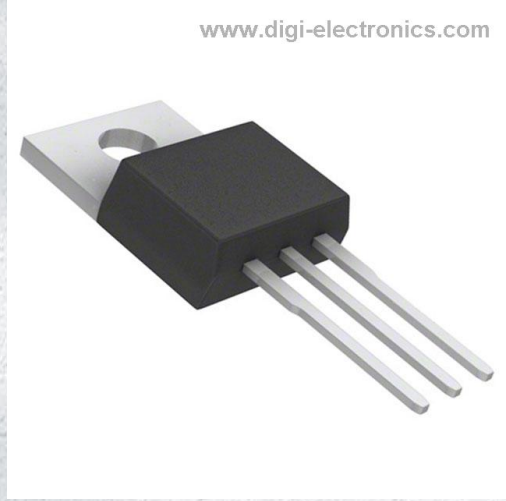
KSB546YTU Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	KSB546YTU-DG
Manufacturer	onsemi
Manufacturer Product Number	KSB546YTU
Description	TRANS PNP 150V 2A TO220-3
Detailed Description	Bipolar (BJT) Transistor PNP 150 V 2 A 5MHz 25 W Through Hole TO-220-3

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
KSB546YTU	onsemi
Series:	Product Status:
-	Last Time Buy
Transistor Type:	Current - Collector (Ic) (Max):
PNP	2 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ Ib, Ic:
150 V	1V @ 50mA, 500mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
50µA (ICBO)	120 @ 400mA, 10V
Power - Max:	Frequency - Transition:
25 W	5MHz
Operating Temperature:	Mounting Type:
150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-220-3	TO-220-3
Base Product Number:	
KSB546	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	Not Applicable
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

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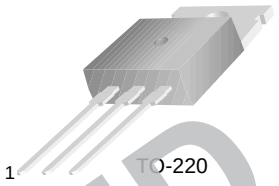
Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

KSB546

TV Vertical Deflection Output

- Collector-Base Voltage : V_{CBO} = -200V
- Collector Current : I_C = -2A
- Collector Dissipation : P_C= 25W (T_C=25°C)
- Complement to KSD401



1 TO-220

1.Base 2.Collector 3.Emitter

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	- 200	V
V_{CEO}	Collector-Emitter Voltage	- 150	V
V_{EBO}	Emitter-Base Voltage	- 5	V
I_C	Collector Current(DC)	- 2	A
P_C	Collector Dissipation (T_C=25°C)	25	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	-55 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	I_C = -500μA, I_E = 0	- 200			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = - 10mA, I_B = 0	- 150			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = - 500uA, I_C = 0	- 5			V
I_{CBO}	Collector Cut-off Current	V_{CB} = - 150V, I_E = 0			- 50	μA
h_{FE}	DC Current Gain	V_{CE} = - 10V, I_E = - 0.4A	40		240	
V_{CE}(sat)	Collector-Emitter Saturation Voltage	I_C = - 500mA, I_B = - 50mA			- 1	V
f_T	Current Gain Bandwidth Product	V_{CE} = - 10V, I_C = - 0.4A		5		MHz

h_{FE} Classification

Classification	R	O	Y
h_{FE}	40 ~ 80	70 ~ 140	120 ~ 240

Typical Characteristics

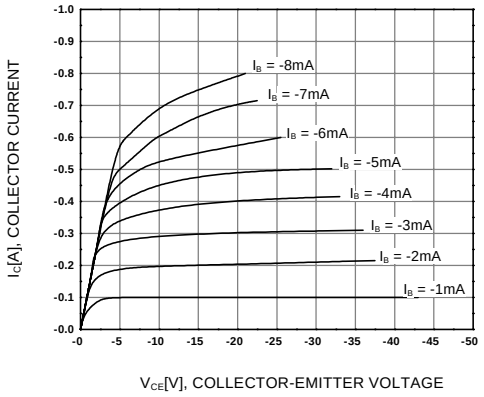


Figure 1. Static Characteristic

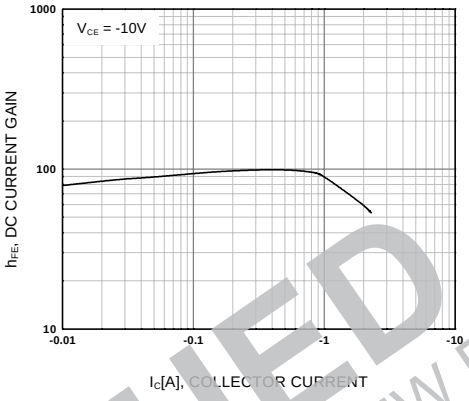


Figure 2. DC current Gain

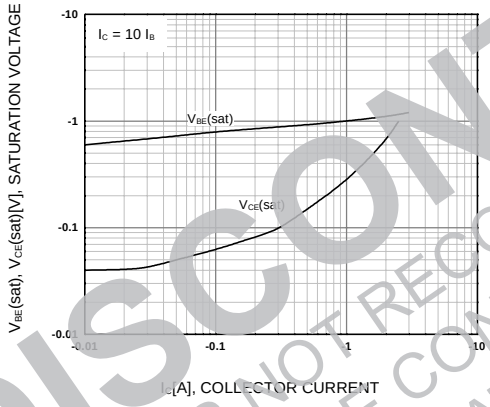


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

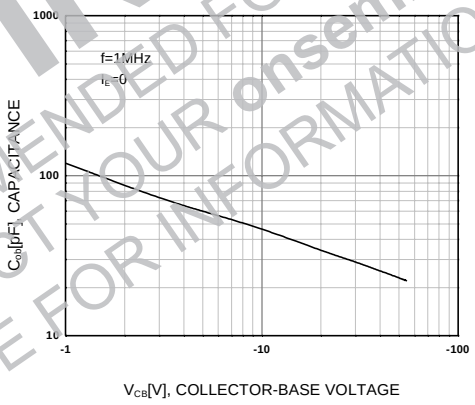


Figure 4. Collector Output Capacitance

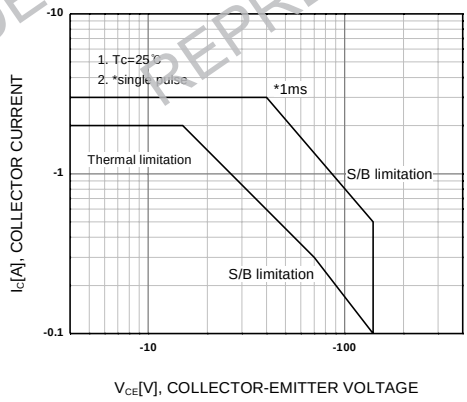


Figure 5. Safe Operating Area

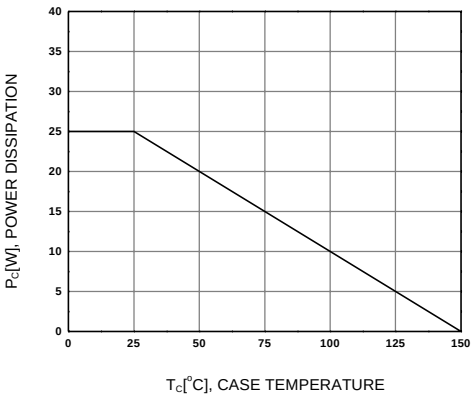
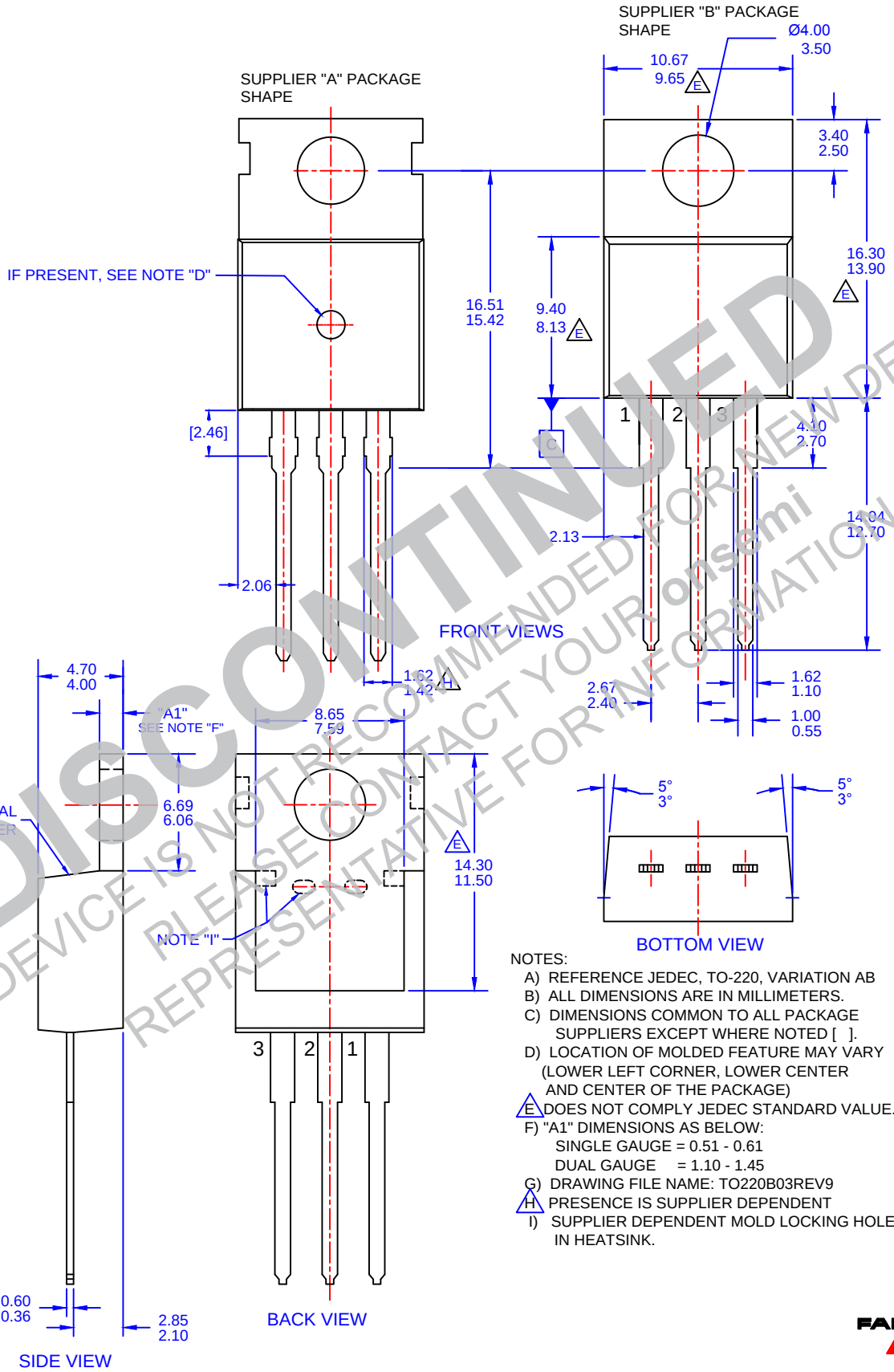


Figure 6. Power Derating



NOTES:

A) REFERENCE JEDEC, TO-220, VARIATION AB
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [ ].
D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
E) DOES NOT COMPLY JEDEC STANDARD VALUE.
F) "A1" DIMENSIONS AS BELOW:
SINGLE GAUGE = 0.51 - 0.61
DUAL GAUGE = 1.10 - 1.45
G) DRAWING FILE NAME: TO220B03REV9
H) PRESENCE IS SUPPLIER DEPENDENT
I) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

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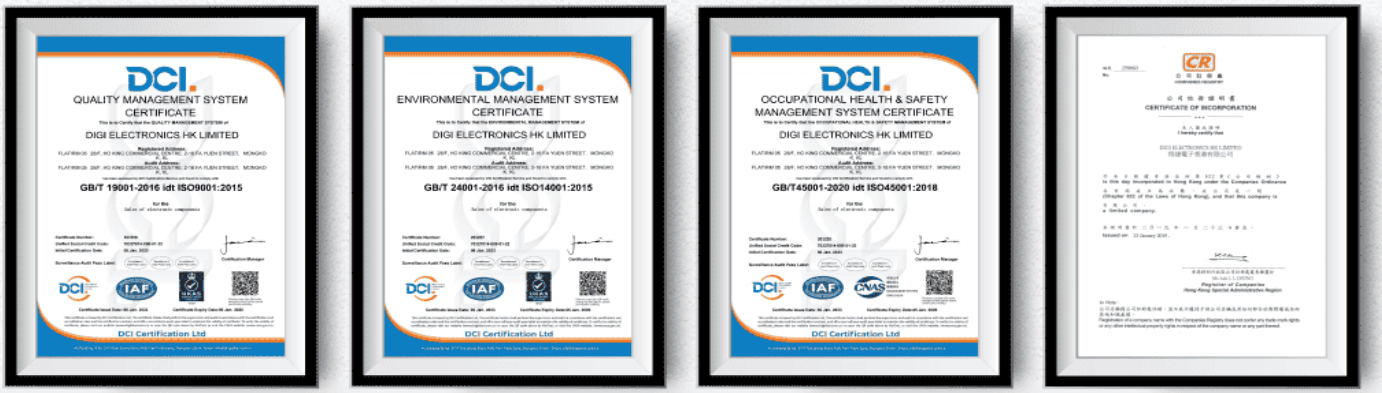

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